

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device wiring board wherein an opening is defined at a predetermined position of a film-like insulating substrate, an electric wiring provided with a connection terminal covering the opening is disposed on a principal plane of the insulating substrate, and a conductive member electrically connected with the connection terminal of the electric wiring is disposed inside the opening, comprising:

 said conductive member and a plating layer having a thickness from a surface on which said electric wiring of the insulating substrate has been disposed being thinner than that of said insulating substrate so as to prevent said conductive member and said plating layer from projecting from the surface opposite to the surface on which said electric wiring is formed, and said conductive member and a soldering paste applied on an electric wiring of a mount board are electrically connected by soaking up part of said soldering paste into said opening.

2. (Previously Amended) A wiring board as claimed in claim 1, wherein:

 a thickness of said conductive member is 1/2 or more of that of said insulating substrate.

3. (Original) A wiring board as claimed in claim 1, wherein:

 said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

4. (Original) A wiring board as claimed in claim 2, wherein:
said conductive member has a thinner thickness at the central portion of
said opening than that of a vicinity of a side wall of said opening.
5. (Original) A wiring board as claimed in claim 1, wherein:
said conductive member is made from any member selected from the
group consisting of copper (Cu), nickel (Ni), and silver (Ag).
6. (Original) A wiring board as claimed in claim 2, wherein:
said conductive member is made from any member selected from the
group consisting of copper (Cu), nickel (Ni), and silver (Ag).
7. (Original) A wiring board as claimed in claim 3, wherein:
said conductive member is made from any member selected from the
group consisting of copper (Cu), nickel (Ni), and silver (Ag).
8. (Original) A wiring board as claimed in claim 1, wherein:
a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au)
are sequentially disposed on a surface of said conductive member.
9. (Original) wiring board as claimed in claim 2, wherein:
a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au)
are sequentially disposed on a surface of said conductive member.
10. (Original) A wiring board as claimed in claim 3, wherein:
a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au)
are sequentially disposed on a surface of said conductive member.
11. (Original) A wiring board as claimed in claim 4, wherein:
a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au)
are sequentially disposed on a surface of said conductive member.

12. (Currently Amended) A semiconductor device wherein a wiring board in which an opening is defined at a predetermined position of a film-like insulating substrate, an electric wiring provided with a connection terminal covering said opening is disposed on a principal plane of said insulating substrate, and a conductive member electrically connected with the connection terminal of said electric wiring is disposed inside the opening is placed; a semiconductor chip is placed on the surface of said wiring board on which said electric wiring has been disposed; the electric wiring of said wiring board is electrically connected with an external electrode of the semiconductor chip; and said semiconductor chip, said electric wiring, and a connecting section for said electric wiring and said external electrode of the semiconductor chip are sealed with a sealing insulator, comprising:

said conductive member and a plating layer having a thickness from a surface on which said electric wiring of the insulating substrate has been formed being thinner than that of said insulating substrate so as to prevent said conductive member and said plating layer from projecting from the surface opposite to the surface on which said electric wiring is formed, and said conductive member and a soldering paste applied on an electric wiring of a mount board are electrically connected by soaking up part of said soldering paste into said opening.

13. (Original) A semiconductor device as claimed in claim 12, wherein:

said semiconductor chip is placed in such that a surface opposed to the surface on which said external electrode has been formed is opposed to said wiring board; and

said external electrode is connected with said electric wiring by means of a bonding wire.

14. (Original) A semiconductor device as claimed in claim 12, wherein:

said semiconductor chip is placed in such that said external electrode thereof is opposed to said wiring board; and

said external electrode is connected with said electric wiring by means of a protrusion conductor.

15. (Original) A semiconductor device as claimed in claim 8, wherein: a thickness of said conductive member is 1/2 or more of that of said insulating substrate.

16. (Original) A semiconductor device as claimed in claim 12, wherein: a thickness of said conductive member is 1/2 or more of that of said insulating substrate.

17. (Original) A semiconductor device as claimed in claim 13, wherein: a thickness of said conductive member is 1/2 or more of that of said insulating substrate.

18. (Original) A semiconductor device as claimed in claim 14, wherein: a thickness of said conductive member is 1/2 or more of that of said insulating substrate.

19. (Original) A semiconductor device as claimed in claim 8, wherein: said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

20. (Original) A semiconductor device as claimed in claim 12, wherein: said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

21. (Original) A semiconductor device as claimed in claim 13, wherein: said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

22. (Original) A semiconductor device as claimed in claim 14, wherein:
said conductive member has a thinner thickness at the central portion of
said opening than that of a vicinity of a side wall of said opening.

23. (Original) A semiconductor device as claimed in claim 15, wherein:
said conductive member has a thinner thickness at the central portion of
said opening than that of a vicinity of a side wall of said opening.

24. (Original) A semiconductor device as claimed in claim 8, wherein:
said conductive member is made from any member selected from the
group consisting of copper (Cu), nickel (Ni), and silver (Ag).

25. (Original) A semiconductor device as claimed in claim 12, wherein:
said conductive member is made from any member selected from the
group consisting of copper (Cu), nickel (Ni), and silver (Ag).

26. (Original) A semiconductor device as claimed in claim 13, wherein:
said conductive member is made from any member selected from the
group consisting of copper (Cu), nickel (Ni), and silver (Ag).

27. (Original) A semiconductor device as claimed in claim 14, wherein:
said conductive member is made from any member selected from the
group consisting of copper (Cu), nickel (Ni), and silver (Ag).

28. (Original) A semiconductor device as claimed in claim 15, wherein:
said conductive member is made from any member selected from the
group consisting of copper (Cu), nickel (Ni), and silver (Ag).

29. (Original) A semiconductor device as claimed in claim 19, wherein:
said conductive member is made from any member selected from the
group consisting of copper (Cu), nickel (Ni), and silver (Ag).

30. (Original) A semiconductor device as claimed in claim 8, wherein:
a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au)
are sequentially disposed on a surface of said conductive member.

31. (Original) A semiconductor device as claimed in claim 12, wherein:
a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au)
are sequentially disposed on a surface of said conductive member.

32. (Original) A semiconductor device as claimed in claim 13, wherein:
a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au)
are sequentially disposed on a surface of said conductive member.

33. (Original) A semiconductor device as claimed in claim 14, wherein:
a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au)
are sequentially disposed on a surface of said conductive member.

34. (Original) A semiconductor device as claimed in claim 15, wherein:
a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au)
are sequentially disposed on a surface of said conductive member.

35. (Original) A semiconductor device as claimed in claim 19, wherein:
a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au)
are sequentially disposed on a surface of said conductive member.

36. (Original) A semiconductor device as claimed in claim 24, wherein:
a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au)
are sequentially disposed on a surface of said conductive member.

Claims 37 – 49 (Cancelled)